TOSHIBA Field Effect Transistor Silicon N-Channel MOS Type (U-MOS VI-H)

# **TPCA8045-H**

High-Efficiency DC-DC Converter Applications Notebook PC Applications Portable Equipment Applications

- Small footprint due to a small and thin package
- High-speed switching
- Small gate charge: Q<sub>SW</sub> = 23 nC (typ.)
- Low drain-source ON-resistance:  $R_{DS}$  (ON) = 2.4  $m\Omega$  (typ.)
- High forward transfer admittance:  $|Y_{fS}| = 136 \text{ S (typ.)}$
- Low leakage current:  $I_{DSS} = 10 \,\mu A \,(max) \,(V_{DS} = 40 \,V)$
- Enhancement mode:  $V_{th} = 1.3 \text{ to } 2.3 \text{ V } (V_{DS} = 10 \text{ V}, I_D = 1.0 \text{ mA})$

### **Absolute Maximum Ratings (Ta = 25°C)**

| Characte                | eristic                      | Symbol           | Rating     | Unit |  |
|-------------------------|------------------------------|------------------|------------|------|--|
| Drain-source voltage    |                              | $V_{DSS}$        | 40         | V    |  |
| Drain-gate voltage (R   | GS = 20 kΩ)                  | $V_{DGR}$        | 40         | V    |  |
| Gate-source voltage     |                              | V <sub>GSS</sub> | ±20        | V    |  |
| Drain current           | DC (Note 1)                  | ΙD               | 46         | А    |  |
| Drain current           | Pulsed (Note 1)              | $I_{DP}$         |            |      |  |
| Drain power dissipation | on (Tc = 25°C)               | $P_{D}$          | 45         | W    |  |
| Drain power dissipation | on $(t = 10 s)$<br>(Note 2a) | $P_{D}$          | 2.8        | W    |  |
| Drain power dissipation | on (t = 10 s)<br>(Note 2b)   | P <sub>D</sub>   | 1.6        | W    |  |
| Single-pulse avalance   | ne energy<br>(Note 3)        | E <sub>AS</sub>  | 196        | mJ   |  |
| Avalanche current       |                              | I <sub>AR</sub>  | 46         | Α    |  |
| Repetitive avalanche    | energy<br>c = 25°C) (Note 4) | E <sub>AR</sub>  | 3.63       | mJ   |  |
| Channel temperature     |                              | T <sub>ch</sub>  | 150        | °C   |  |
| Storage temperature     | range                        | T <sub>stg</sub> | -55 to 150 | °C   |  |

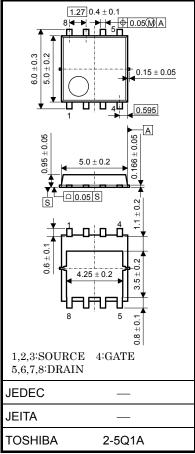
Note: For Notes 1 to 4, refer to the next page.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the

reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

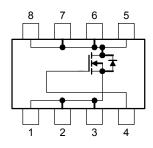
This transistor is an electrostatic-sensitive device. Handle with care.

Unit: mm



Weight: 0.069 g (typ.)

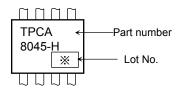
#### **Circuit Configuration**



#### **Thermal Characteristics**

| Characteristic  | Symbol                 | Max  | Unit |
|---|------------------------|------|------|
| Thermal resistance, channel to case (Tc = 25°C)                       | R <sub>th (ch-c)</sub> | 2.78 | °C/W |
| Thermal resistance, channel to ambient $(t=10\;s) \eqno(Note\;2a)$    | R <sub>th (ch-a)</sub> | 44.6 | °C/W |
| Thermal resistance, channel to ambient $(t = 10 \text{ s})$ (Note 2b) | R <sub>th (ch-a)</sub> | 78.1 | °C/W |

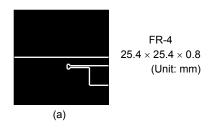
### Marking (Note 5)

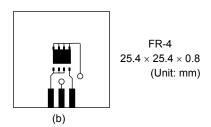


Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: (a) Device mounted on a glass-epoxy board (a)

(b) Device mounted on a glass-epoxy board (b)

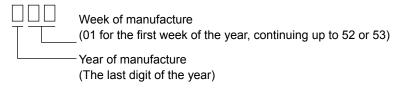




Note 3:  $V_{DD}$  = 24 V,  $T_{ch}$  = 25°C (initial), L = 100  $\mu$ H,  $R_G$  = 25  $\Omega$ ,  $I_{AR}$  = 46 A

Note 4: Repetitive rating: pulse width limited by maximum channel temperature

Note 5: \* Weekly code: (Three digits)



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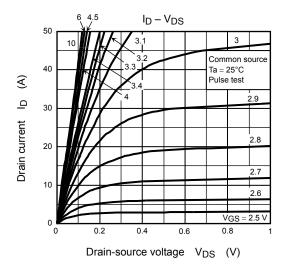
# **Electrical Characteristics (Ta = 25°C)**

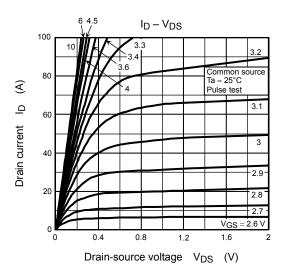
| Ch                             | aracteristic   | Symbol   | Test Condition   | Min | Тур.   | Max  | Unit |
|--------------------------------|--|--|--|-----|--|------|------|
| Gate leakage cur               | rent   | I <sub>GSS</sub>   | $V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$                        | _   | _  | ±100 | nA   |
| Drain cutoff curre             | ent  | I <sub>DSS</sub>   | V <sub>DS</sub> = 40 V, V <sub>GS</sub> = 0 V                            |     | _  | 10   | μА   |
| Drain agurag bro               | akdowa voltago   | V (BR) DSS   | $I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$                              | 40  | - ±100 - 10 0 10 5 23 - 2.9 4.1 - 2.4 3.6 8 136 - 5800 7540 - 305 445 - 950 - 1.0 1.5 - 4.6 15 11 67 | V    |      |
| Drain-source breakdown voltage |  | V (BR) DSX   | $I_D = 10 \text{ mA}, V_{GS} = -20 \text{ V}$                            | 25  | _  | _    | v    |
| Gate threshold vo              | oltage   | V <sub>th</sub>  | $V_{DS} = 10 \text{ V}, I_D = 1.0 \text{ mA}$                            | 1.3 | _  | 2.3  | ٧    |
| Drain cource ON                | rosistanco   | Pro (OV)   | $V_{GS} = 4.5 \text{ V}, I_D = 23 \text{ A}$                             | _   | 2.9  | 4.1  | m0   |
| Drain-source ON-resistance     |  | KDS (ON)   | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 23 A                            | _   | 2.4  | 3.6  | mΩ   |
| Forward transfer               | admittance   | Y <sub>fs</sub>  | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 23 A                            | 68  | 136  | _    | S    |
| Input capacitance              | 9  | C <sub>iss</sub>   |  | _   | 5800   | 7540 |      |
| Reverse transfer capacitance   |  | C <sub>rss</sub>   | $V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$         | _   | 305  | 445  | pF   |
| Output capacitance             |  | Coss   |  | _   | 950  | _    |      |
| Gate resistance                |  | rg   | V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V, f = 1 MHz                 | _   | 1.0  | 1.5  | Ω    |
|                                | Rise time  | t <sub>r</sub>   | 10 V □ lp = 23 A   | _   | 4.6  | _    |      |
| Switching time                 | $ \begin{array}{c ccccccccccccccccccccccccccccccccccc$ | _  |  |     |  |      |      |
| Switching time                 | Fall time  | t <sub>f</sub>   | RL = 0.8   | _   | 11   |      | ns   |
|                                | Turn-off time  | t <sub>off</sub>   |  | _   | 67   | _    |      |
| Total gate charge              | ·<br>}   | 0  | $V_{DD} \approx 32 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 46 \text{ A}$ | _   | 90   | _    |      |
| (gate-source plus              | gate-drain)  | Qg   | $V_{DD} \approx 32 \text{ V}, V_{GS} = 5 \text{ V}, I_D = 46 \text{ A}$  | _   | 47   | _    |      |
| Gate-source charge 1           |  | Q <sub>gs1</sub>   | $V_{DD} \approx 32 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 46 \text{ A}$ | _   | 16   | _    | nC   |
| Gate-drain ("Miller") charge   |  | Q <sub>gd</sub>  |  | _   | 15   | _    |      |
| Gate switch charg              | ge   | $Q_{g} = \begin{array}{c} \text{Duty} \le 1\%,  t_{W} = 10  \mu\text{s} \\ \\ \text{V}_{DD} \approx 32  \text{V},  \text{V}_{GS} = 10  \text{V},  \text{I}_{D} = 46  \text{A} &$ |  | 23  | _  |      |      |

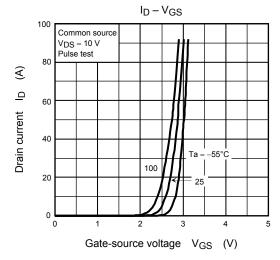
## **Source-Drain Ratings and Characteristics (Ta = 25°C)**

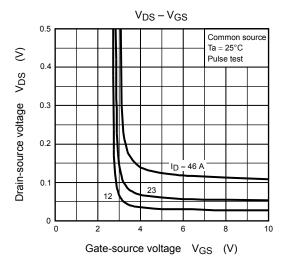
| Characteristic          |       | Symbol   | Test Condition   | Min   | Тур. | Max | Unit |   |
|-------------------------|-------|----------|------------------|---|------|-----|------|---|
| Drain reverse current   | Pulse | (Note 1) | I <sub>DRP</sub> | _   | _    | _   | 138  | Α |
| Forward voltage (diode) |       |          | $V_{DSF}$        | $I_{DR} = 46 \text{ A}, V_{GS} = 0 \text{ V}$ |      | _   | -1.2 | V |

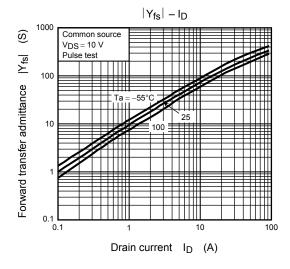
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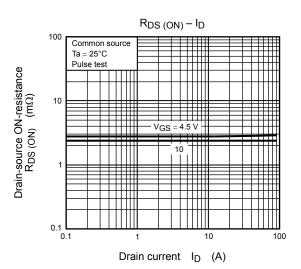


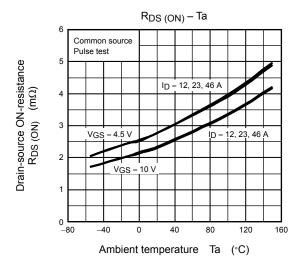


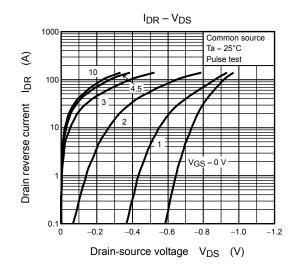


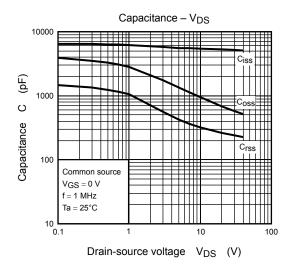


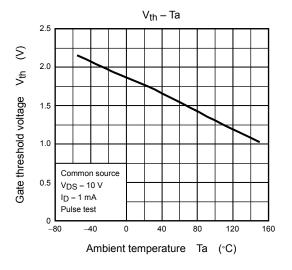


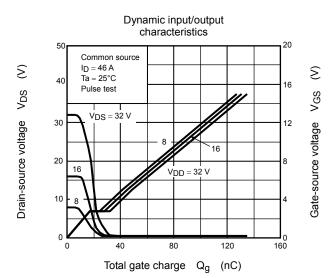




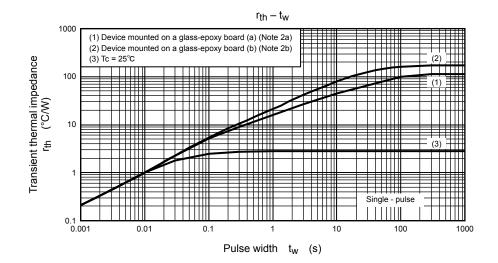


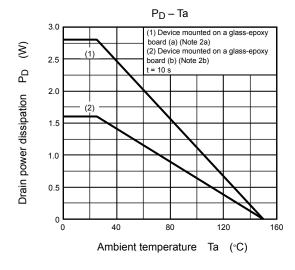


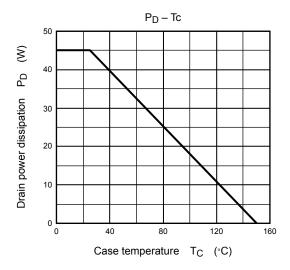


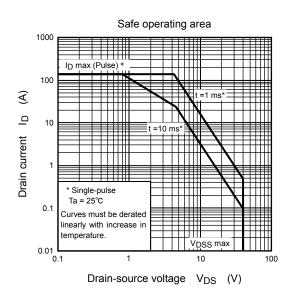


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